

AMENDMENTS TO THE CLAIMS

The listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims

1. (Currently Amended) A semiconductor apparatus comprising:
 - a semiconductor chip including a power semiconductor device constructed by using a wide band gap semiconductor;
 - a base material made of an electrically conductive material and electrically connected to a part of [[a]] one main face of said semiconductor chip;
 - a heat conducting member coming in contact with a part of the other main face of said semiconductor chip and releasing heat directly from said semiconductor chip without by way of said base material; and
 - an encapsulating material for encapsulating said semiconductor chip and said heat conducting member,
- wherein a part of said base material is extruded outside said encapsulating material and works as an external connection terminal, and
- wherein a first intermediate member made of an electrically conductive material and a second intermediate member made of a material having lower heat conductivity than said first intermediate member are provided between said base material and said semiconductor chip.

2. (Original) The semiconductor apparatus of Claim 1,
wherein said power semiconductor device has a region where a current passes at a current density of 50 A/cm^2 or more.

3. (Original) The semiconductor apparatus of Claim 1 or 2,
wherein said encapsulating material is made of a resin or glass, and
said heat conducting member is exposed from said encapsulating material.

4. (Original) The semiconductor apparatus of Claim 3, further comprising a radiation fin
that is in contact with said heat conducting member and is extruded outside said encapsulating
material.

5. (Original) The semiconductor apparatus of Claim 1 or 2, further comprising a film for
covering said encapsulating material.

6. (Original) The semiconductor apparatus of Claim 5, further comprising a radiation fin
opposing said heat conducting member with said film sandwiched therebetween.

7. (Cancelled)

8. (Withdrawn) The semiconductor apparatus of claim 1,
wherein a contact area between said semiconductor chip and said base material is smaller
than a half of an area of said semiconductor chip.

9. (Withdrawn) The semiconductor apparatus of claim 1,
wherein said power semiconductor device is a vertical element, and
said semiconductor apparatus further comprises another semiconductor chip that is
stacked on said semiconductor chip and a part of which is connected to said base material.

10. (Withdrawn) The semiconductor apparatus of claim 1,
wherein said external connection terminal of said base material is constructed to be
mounted on a print wiring board.

11. (Withdrawn) The semiconductor apparatus of claim 1,
wherein said wide band gap semiconductor is SiC.

12. (Withdrawn) A semiconductor apparatus comprising:
a semiconductor chip including a power semiconductor device constructed by using a
wide band gap semiconductor;
a base material made of an electrically conductive material and connected to a part of a
face of said semiconductor chip;
a heat conducting member in contact with a part of the face of said semiconductor chip;
a vessel in contact with said heat conducting member and encapsulating said
semiconductor chip, said base material and said heat conducting member; and
an external connection terminal electrically connected to said base material and extruded
from said vessel.

13. (Withdrawn) The semiconductor apparatus of Claim 12,
wherein a region around said semiconductor chip, said base material and said heat
conducting member within said vessel is filled with glass, a resin, an inert gas or a gas reduced in
pressure.

14. (Withdrawn) The semiconductor apparatus of Claim 12 or 13, further comprising a
radiation fin opposing said heat conducting member with a part of said vessel sandwiched
therebetween.

15. (New) The semiconductor apparatus of claim 1,
wherein another heat conducting member is in direct contact with the one main face of
said semiconductor chip.

16. (New) The semiconductor apparatus of claim 1,
wherein a contact area between said semiconductor chip and said base material is smaller
than a half of an area of the upper or lower surface of said semiconductor chip.

17. (New) The semiconductor apparatus of claim 1,
wherein said power semiconductor device is a vertical element, and
said semiconductor apparatus further comprises another semiconductor chip that is
stacked on said semiconductor chip and a part of which is connected to said base material.

18. (New) The semiconductor apparatus of claim 1,
wherein said external connection terminal of said base material is constructed to be
mounted on a print wiring board.

19. (New) The semiconductor apparatus of claim 1,
wherein said wide band gap semiconductor is SiC.